International
IOR Rectifier

Data Sheet No. PD60265

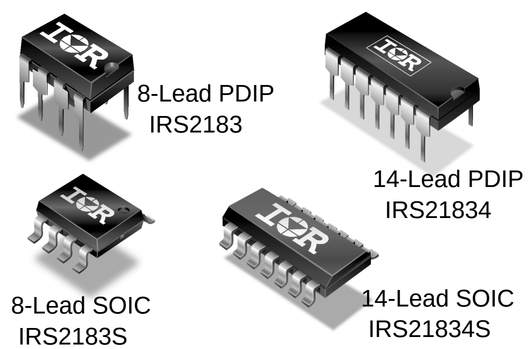
IRS2183/IRS21834(S)PbF

HALF-BRIDGE DRIVER

Features

- Floating channel designed for bootstrap operation
- Fully operational to +600 V
- Tolerant to negative transient voltage, dV/dt immune
- Gate drive supply range from 10 V to 20 V
- Undervoltage lockout for both channels
- 3.3 V and 5 V input logic compatible
- Matched propagation delay for both channels
- Logic and power ground +/- 5 V offset
- Lower di/dt gate driver for better noise immunity
- Output source/sink current capability 1.4 A/1.8 A
- RoHS compliant

Packages



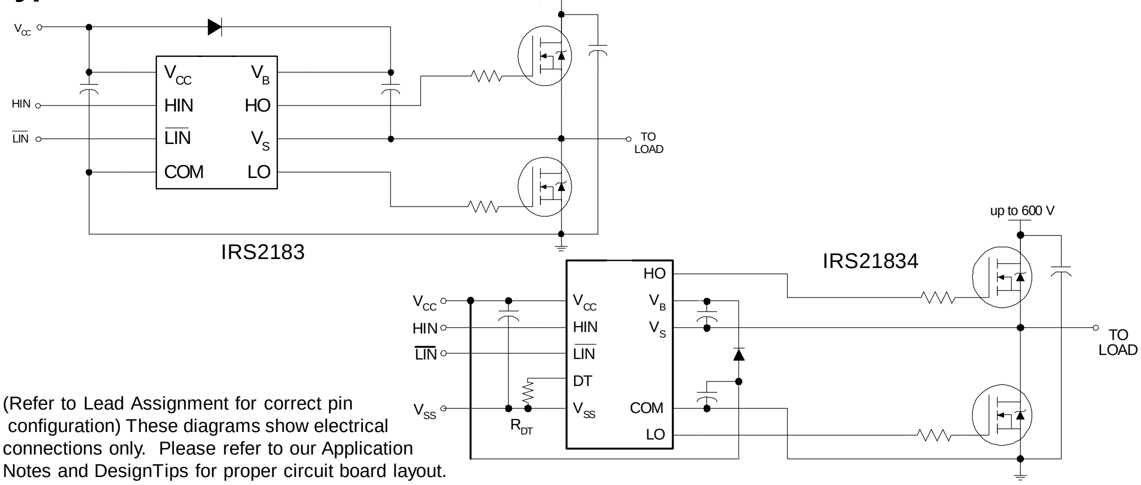
Description

The IRS2183/IRS21834 are high voltage, high speed power MOSFET and IGBT drivers with dependent high-side and low-side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3 V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high-side configuration which operates up to 600 V.

Feature Comparison

Part	Input logic	Cross-conduction prevention logic	Deadtime (ns)	Ground Pins	t_{on}/t_{off} (ns)
2181	HIN/LIN	no	none	COM	180/220
21814				V_{SS}/COM	
2183	HIN/$\overline{\text{LIN}}$	yes	Internal 400	COM	180/220
21834			Program 400-5000	V_{SS}/COM	
2184	IN/$\overline{\text{SD}}$	yes	Internal 400	COM	680/270
21844			Program 400-5000	V_{SS}/COM	

Typical Connection



(Refer to Lead Assignment for correct pin configuration) These diagrams show electrical connections only. Please refer to our Application Notes and DesignTips for proper circuit board layout.

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition		Min.	Max.	Units
V_B	High-side floating absolute voltage		-0.3	620 (Note 1)	V
V_S	High-side floating supply offset voltage		V_B - 20	V_B + 0.3	
V_{HO}	High-side floating output voltage		V_S - 0.3	V_B + 0.3	
V_{CC}	Low-side and logic fixed supply voltage		-0.3	20 (Note 1)	
V_{LO}	Low-side output voltage		-0.3	V_{CC} + 0.3	
DT	Programmable deadtime pin voltage (IR21834 only)		V_{SS} - 0.3	V_{CC} + 0.3	
V_{IN}	Logic input voltage (HIN & $\overline{LIN}$)		V_{SS} - 0.3	V_{CC} + 0.3	
V_{SS}	Logic ground (IR21834 only)		V_{CC} - 20	V_{CC} + 0.3	
dV_S/dt	Allowable offset supply voltage transient		—	50	V/ns
P_D	Package power dissipation @ $T_A \leq$ +25 °C	(8-lead PDIP)	—	1.0	W
		(8-lead SOIC)	—	0.625	
		(14-lead PDIP)	—	1.6	
		(14-lead SOIC)	—	1.0	
Rth_{JA}	Thermal resistance, junction to ambient	(8-lead PDIP)	—	125	°C/W
		(8-lead SOIC)	—	200	
		(14-lead PDIP)	—	75	
		(14-lead SOIC)	—	120	
T_J	Junction temperature		—	150	°C
T_S	Storage temperature		-50	150	
T_L	Lead temperature (soldering, 10 seconds)		—	300	

Note 1: All supplies are fully tested at 25 V and an internal 20 V clamp exists for each supply.

Recommended Operating Conditions

The input/output logic timing diagram is shown in Fig. 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15 V differential.

Symbol	Definition	Min.	Max.	Units
V_B	High-side floating supply absolute voltage	V_S + 10	V_S + 20	V
V_S	High-side floating supply offset voltage	Note 2	600	
V_{HO}	High-side floating output voltage	V_S	V_B	
V_{CC}	Low-side and logic fixed supply voltage	10	20	
V_{LO}	Low-side output voltage	0	V_{CC}	
V_{IN}	Logic input voltage (HIN & $\overline{LIN}$)	V_{SS}	V_{CC}	
DT	Programmable deadtime pin voltage (IR21834 only)	V_{SS}	V_{CC}	
V_{SS}	Logic ground (IR21834 only)	-5	5	
T_A	Ambient temperature	-40	125	°C

Note 2: Logic operational for V_S of -5 V to +600 V. Logic state held for V_S of -5 V to $-V_{BS}$. (Please refer to the Design Tip DT97-3 for more details).

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15 V, V_{SS} = COM, C_L = 1000 pF, T_A = 25 °C, DT = V_{SS} unless otherwise specified.

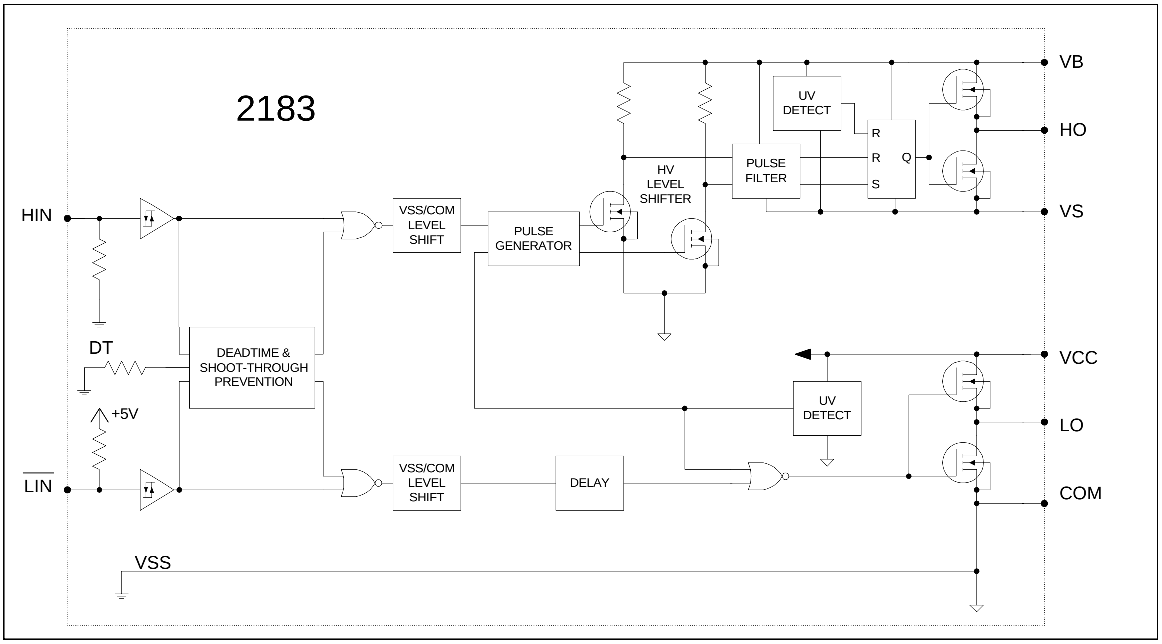
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t_{on}	Turn-on propagation delay	—	180	270	ns	V_S = 0V
t_{off}	Turn-off propagation delay	—	220	330		V_S = 0V or 600V
MT	Delay matching $\lvert t_{on} - t_{off} \rvert$	—	0	35		
t_r	Turn-on rise time	—	40	60		V_S = 0 V
t_f	Turn-off fall time	—	20	35		
DT	Deadtime: LO turn-off to HO turn-on(DT_{LO-HO}) &	280	400	520		R_{DT}= 0 Ω
	HO turn-off to LO turn-on (DT_{HO-LO})	4	5	6	µs	R_{DT} = 200 kΩ (IR21834)
MDT	Deadtime matching = $\lvert DT_{LO-HO} - DT_{HO-LO} \rvert$	—	0	50	ns	R_{DT}=0 Ω
		—	0	600		R_{DT} = 200kΩ (IR21834)

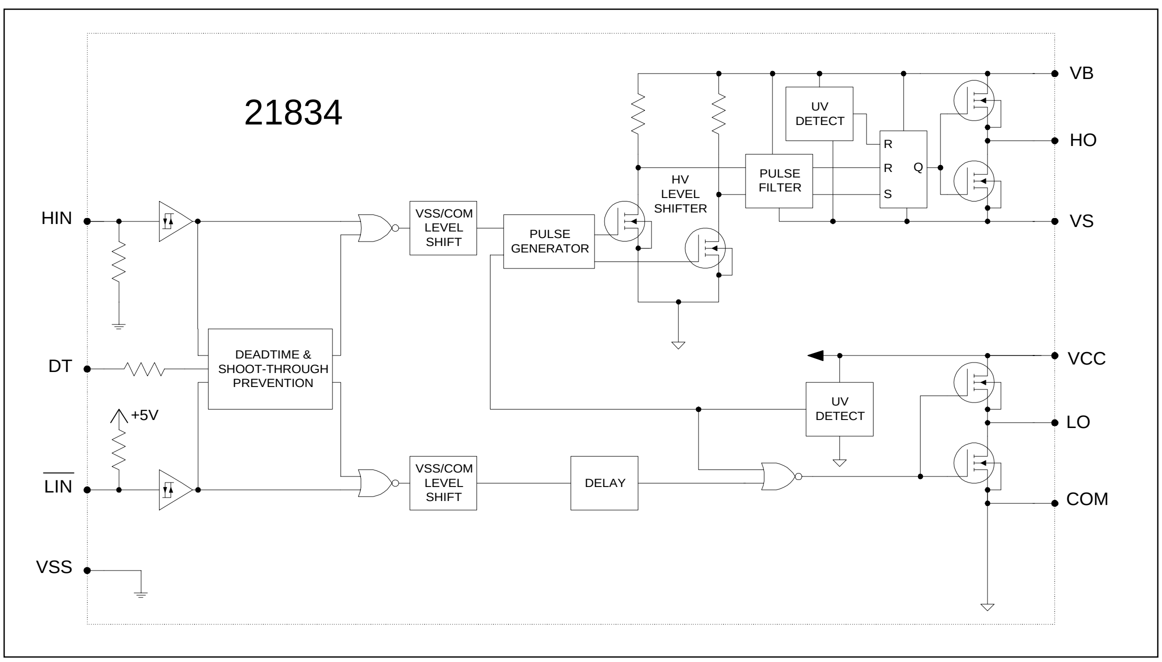
Static Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15 V, V_{SS} = COM, DT= V_{SS} and T_A = 25 °C unless otherwise specified. The V_{IL}, V_{IH}, and I_{IN} parameters are referenced to V_{SS}/COM and are applicable to the respective input leads: HIN and $\overline{\text{LIN}}$. The V_O, I_O, and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V_{IH}	Logic "1" input voltage for HIN & logic "0" for $\overline{\text{LIN}}$	2.5	—	—	V	V_{CC} = 10 V to 20 V
V_{IL}	Logic "0" input voltage for HIN & logic "1" for $\overline{\text{LIN}}$	—	—	0.8		
V_{OH}	High level output voltage, V_{BIAS} - V_O	—	—	1.4		I_O = 0 A
V_{OL}	Low level output voltage, V_O	—	—	0.2		I_O = 20 mA
I_{LK}	Offset supply leakage current	—	—	50	µA	V_B = V_S = 600 V
I_{QBS}	Quiescent V_{BS} supply current	20	60	150		V_{IN} = 0 V or 5 V
I_{QCC}	Quiescent V_{CC} supply current	0.4	1.0	1.6	mA	
I_{IN+}	Logic "1" input bias current	—	25	60	µA	HIN = 5 V, $\overline{\text{LIN}}$ = 0 V
I_{IN-}	Logic "0" input bias current	—	—	5.0		HIN = 0 V, $\overline{\text{LIN}}$ = 5 V
V_{CCUV+} V_{BSUV+}	V_{CC} and V_{BS} supply undervoltage positive going threshold	8.0	8.9	9.8	V	
V_{CCUV-} V_{BSUV-}	V_{CC} and V_{BS} supply undervoltage negative going threshold	7.4	8.2	9.0		
V_{CCUVH} V_{BSUVH}	Hysteresis	0.3	0.7	—		
I_{O+}	Output high short circuit pulsed current	1.4	1.9	—	A	V_O = 0 V, PW ≤ 10 µs
I_{O-}	Output low short circuit pulsed current	1.8	2.3	—		V_O = 15 V, PW ≤ 10 µs

Functional Block Diagrams

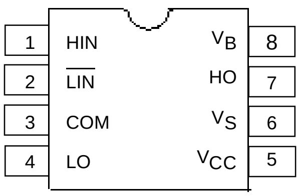




Lead Definitions

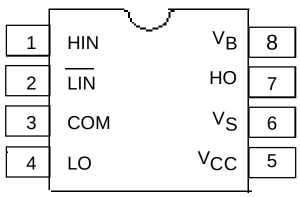
Symbol	Description
HIN	Logic input for high-side gate driver output (HO), in phase (referenced to COM for IRS2183 and VSS for IRS21834)
$\overline{\text{LIN}}$	Logic input for low-side gate driver output (LO), out of phase (referenced to COM for IRS2183 and VSS for IRS21834)
DT	Programmable deadtime lead, referenced to VSS (IRS21834 only)
V_{SS}	Logic ground (IRS21834 only)
V_B	High-side floating supply
HO	High-side gate driver output
V_S	High-side floating supply return
V_{CC}	Low-side and logic fixed supply
LO	Low-side gate driver output
COM	Low-side return

Lead Assignments



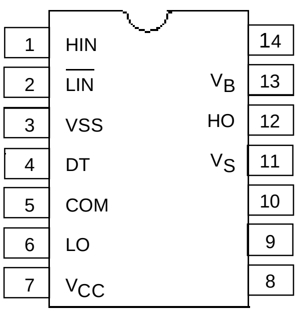
8-Lead PDIP

IRS2183PbF



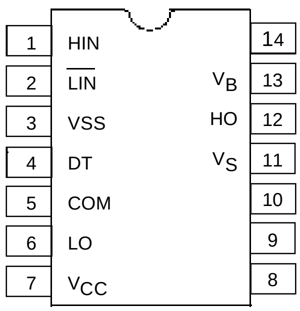
8-Lead SOIC

IRS2183SPbF



14-Lead PDIP

IRS21834PbF



14-Lead SOIC

IRS21834SPbF

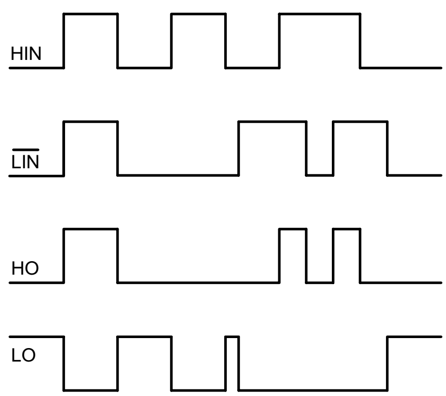


Figure 1. Input/Output Timing Diagram

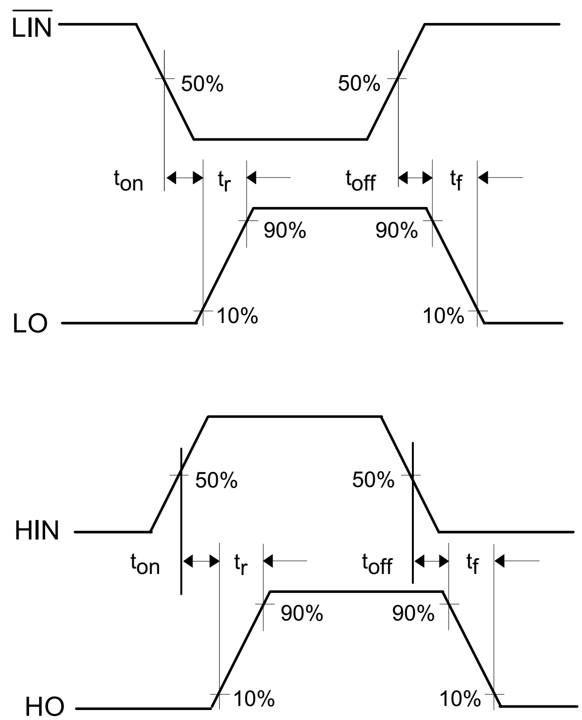


Figure 2. Switching Time Waveform Definitions

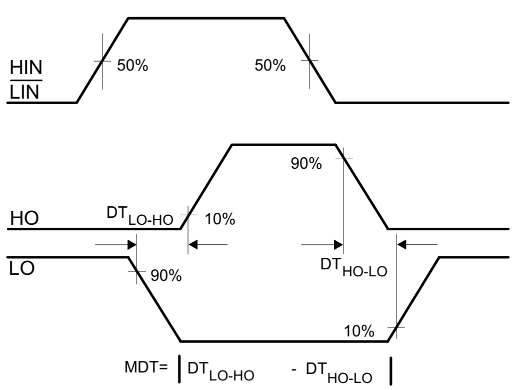


Figure 3. Deadtime Waveform Definitions

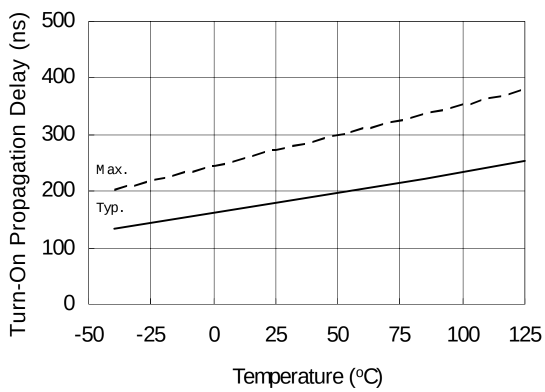


Figure 4A. Turn-On Propagation Delay vs. Temperature

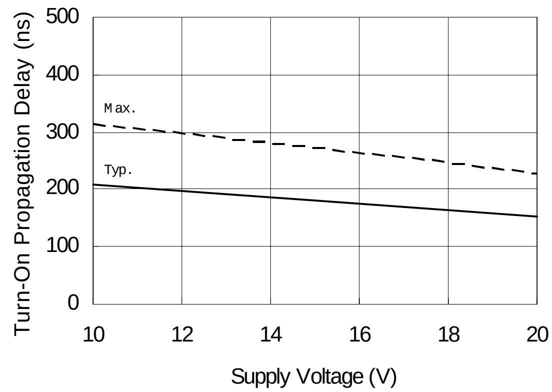


Figure 4B. Turn-On Propagation Delay vs. Supply Voltage

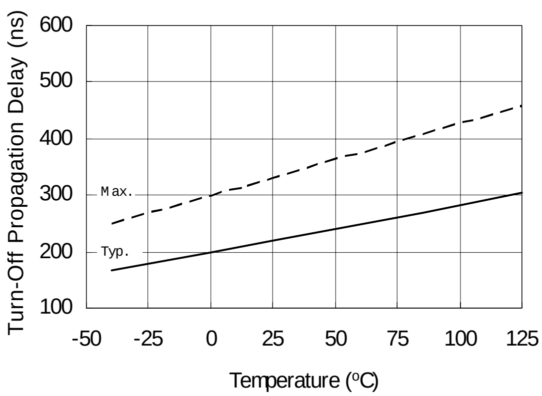


Figure 5A. Turn-Off Propagation Delay vs. Temperature

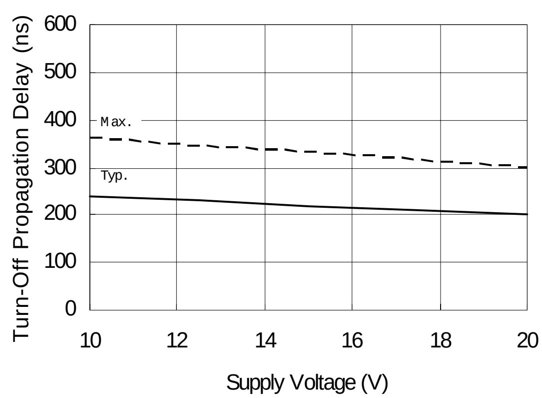


Figure 5B. Turn-Off Propagation Delay vs. Supply Voltage

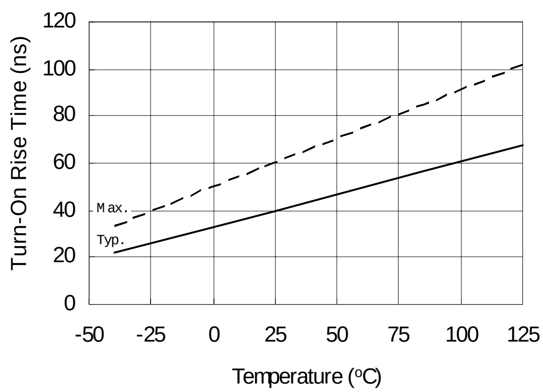


Figure 6A. Turn-On Rise Time vs. Temperature

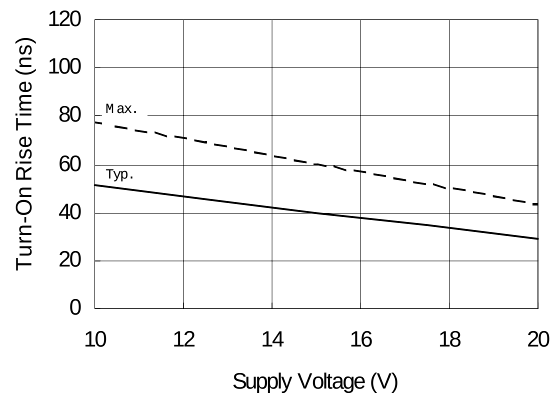


Figure 6B. Turn-On Rise Time vs. Supply Voltage

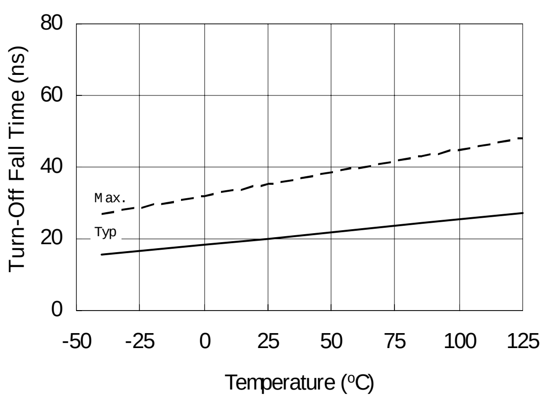


Figure 7A. Turn-Off Fall Time vs. Temperature

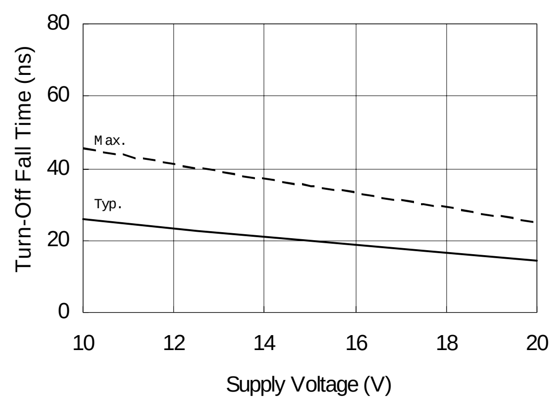


Figure 7B. Turn-Off Fall Time vs. Supply Voltage

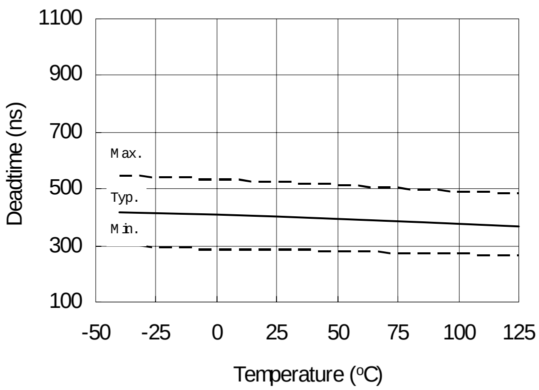


Figure 8A. Deadtime vs. Temperature

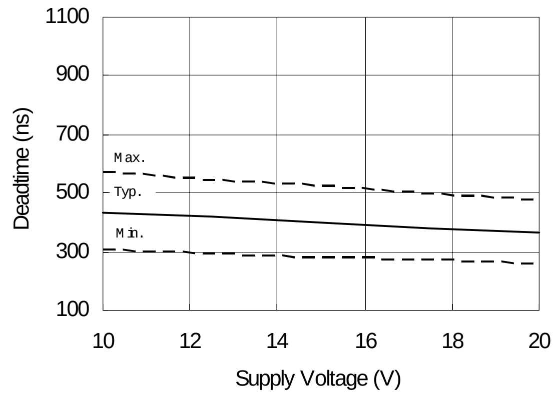


Figure 8B. Deadtime vs. Supply Voltage

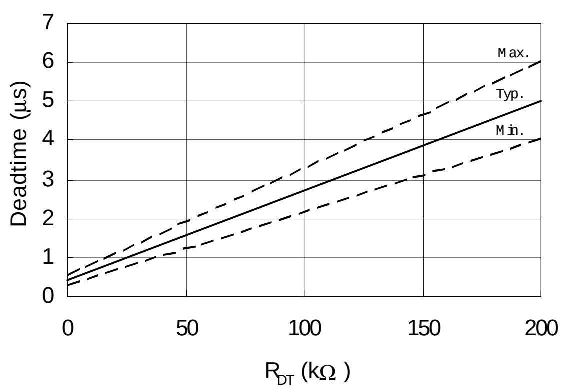


Figure 8C. Deadtime vs. R_{DT}

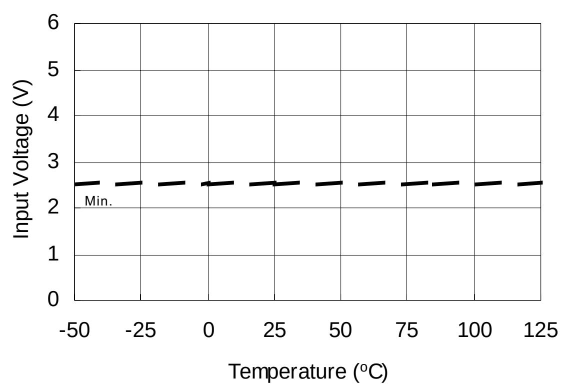


Figure 9A. Logic "1" Input Voltage vs. Temperature

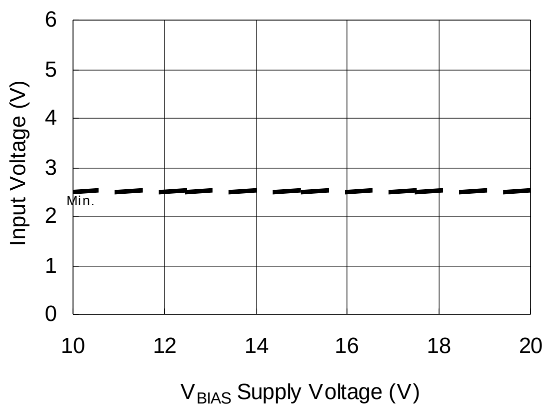


Figure 9B. Logic "1" Input Voltage vs. Supply Voltage

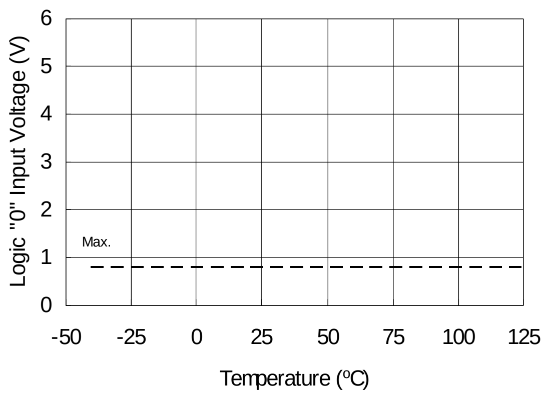


Figure 10A. Logic "0" Input Voltage vs. Temperature

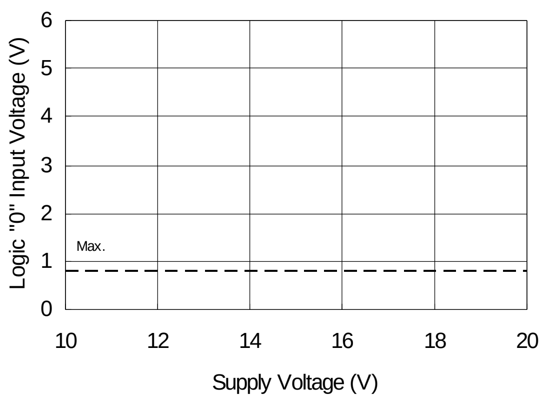


Figure 10B. Logic "0" Input Voltage vs. Supply Voltage

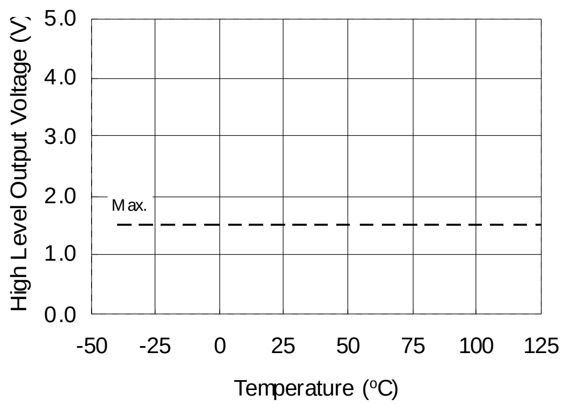


Figure 11A. High Level Output Voltage vs. Temperature (I_O = 0 mA)

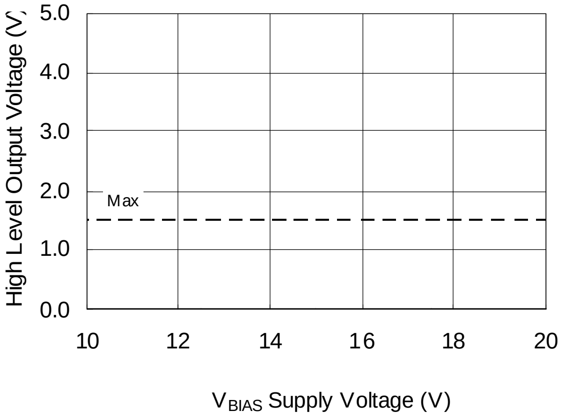


Figure 11B. High Level Output Voltage vs. Supply Voltage (I_o = 0 mA)

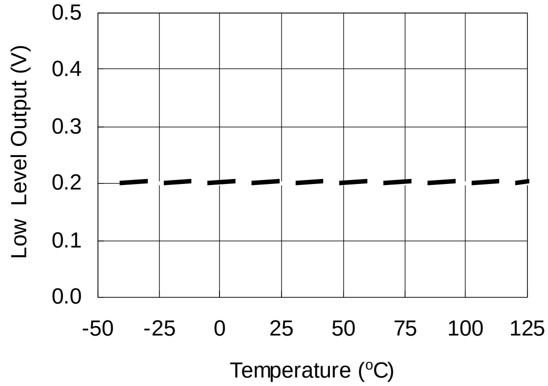


Figure 12A. Low Level Output vs. Temperature

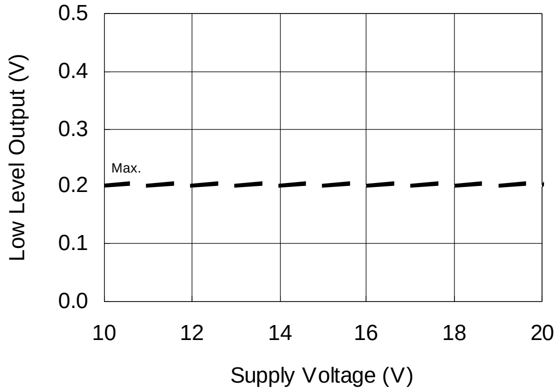


Figure 12B. Low Level Output vs. Supply Voltage

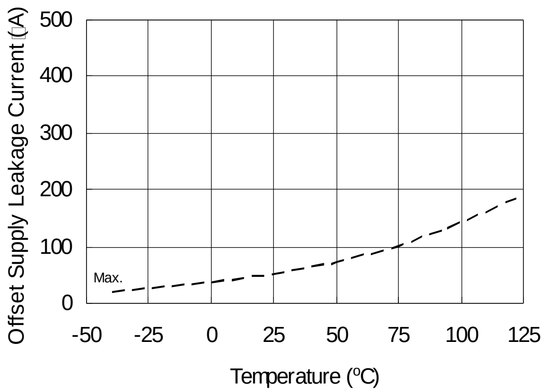


Figure 13A. Offset Supply Leakage Current vs. Temperature

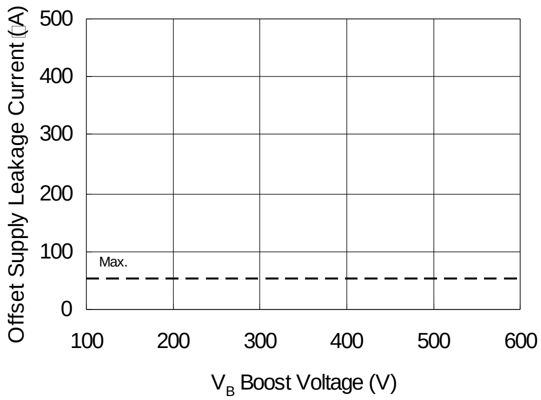


Figure 13B. Offset Supply Leakage Current vs. V_B Boost Voltage

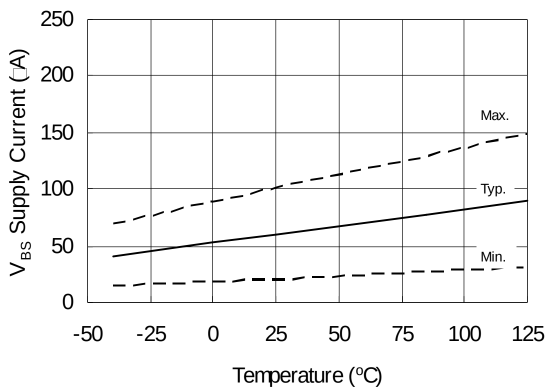


Figure 14A. V_{BS} Supply Current vs. Temperature

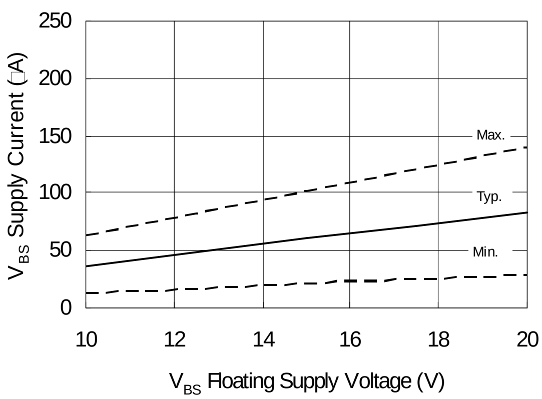


Figure 14B. V_{BS} Supply Current vs. V_{BS} Floating Supply Voltage

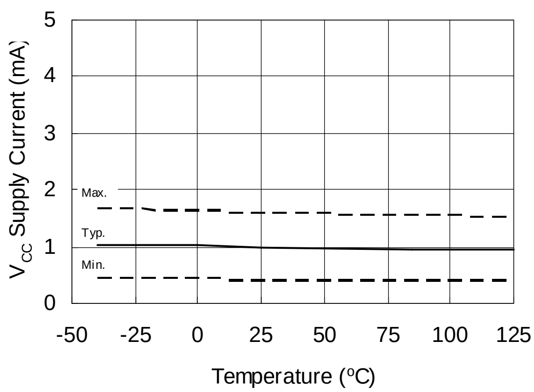


Figure 15A. V_{CC} Supply Current vs. Temperature

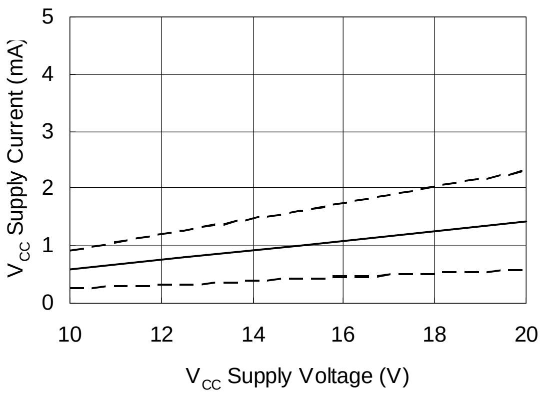


Figure 15B. V_{CC} Supply Current vs. V_{CC} Supply Voltage

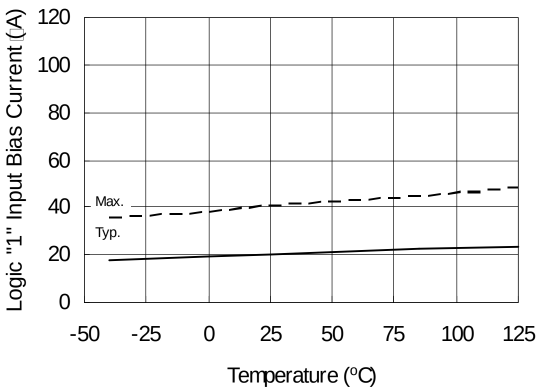


Figure 16A. Logic "1" Input Bias Current vs. Temperature

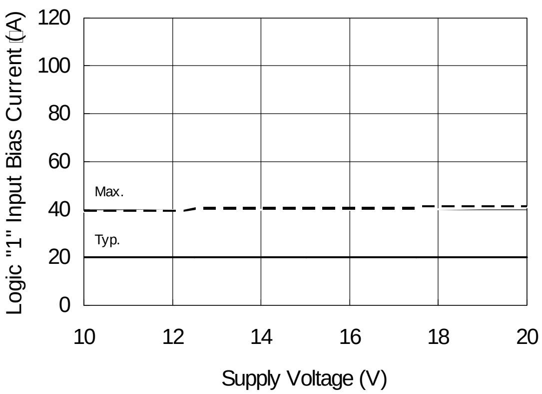


Figure 16B. Logic "1" Input Bias Current vs. Supply Voltage

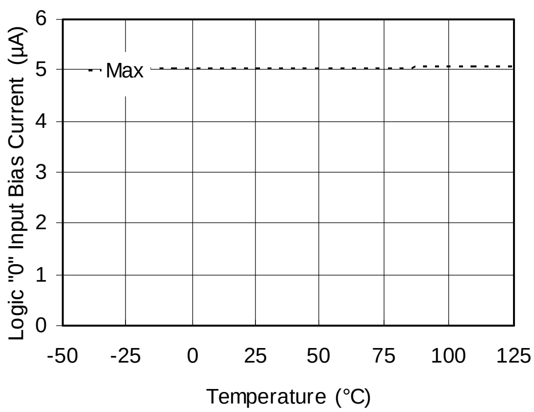


Figure 17A. Logic "0" Input Bias Current vs. Temperature

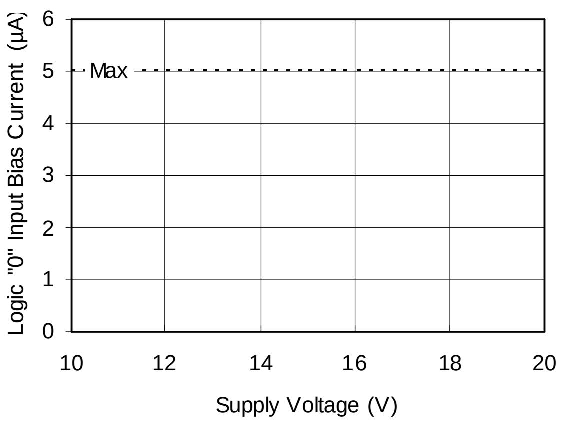


Figure 17B. Logic "0" Input Bias Current vs. Voltage

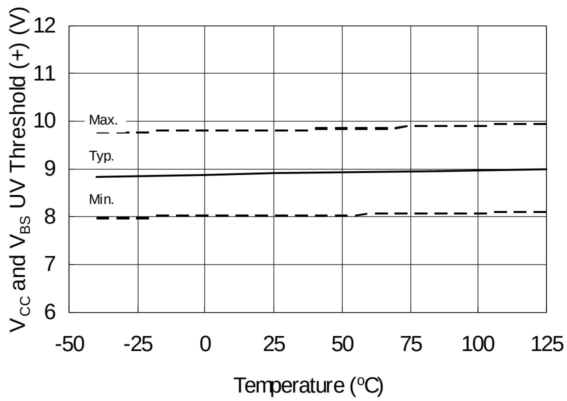


Figure 18. V_{CC} and V_{BS} Undervoltage Threshold (+) vs. Temperature

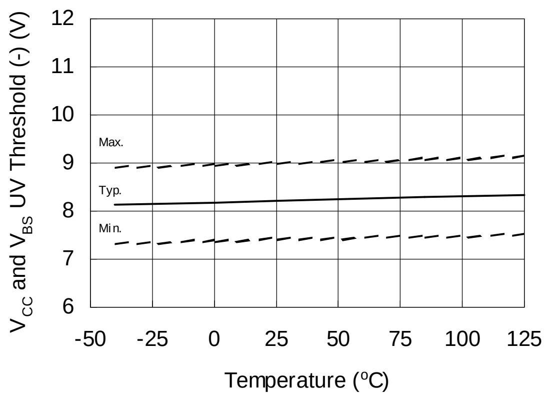


Figure 19. V_{CC} and V_{BS} Undervoltage Threshold (-) vs. Temperature

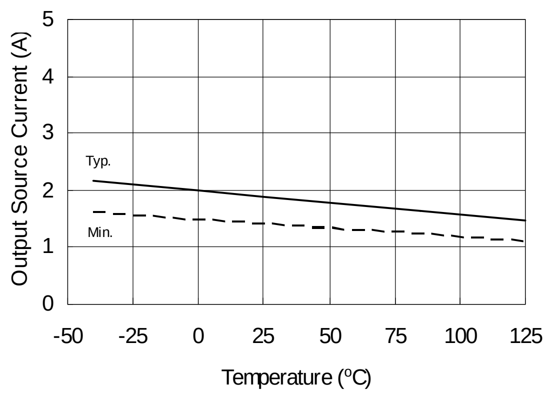


Figure 20A. Output Source Current vs. Temperature

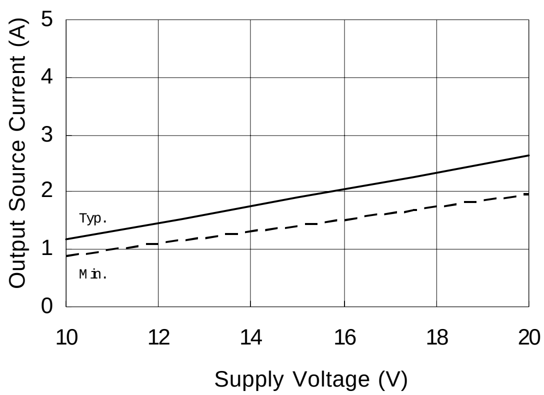


Figure 20B. Output Source Current vs. Supply Voltage

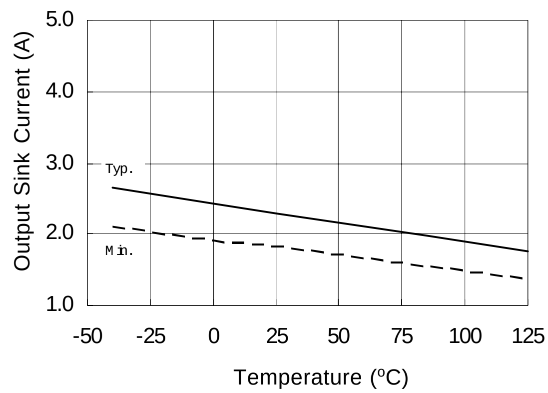


Figure 21A. Output Sink Current vs. Temperature

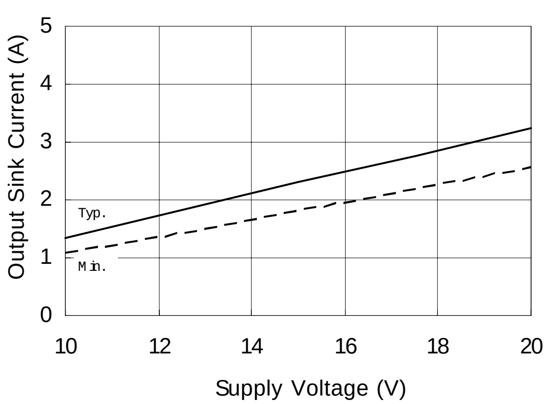


Figure 21B. Output Sink Current vs. Supply Voltage

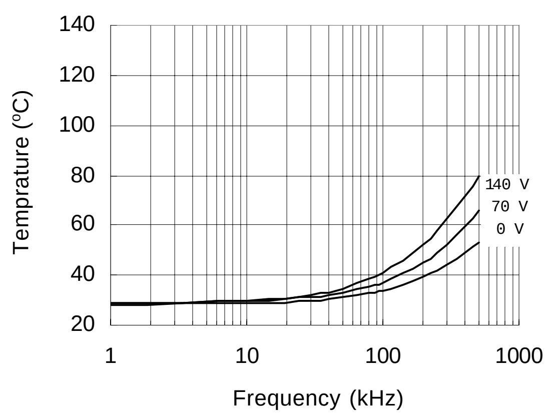


Figure 22. IRS2183 vs. Frequency (IRFBC20), R_{gate}=33 Ω, V_{CC}=15 V

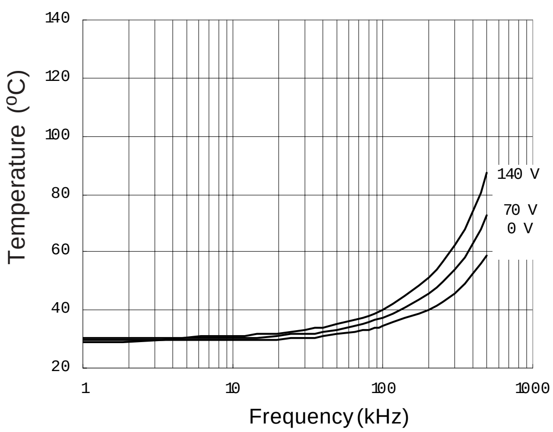


Figure 23. IRS2183 vs. Frequency (IRFBC30), R_{gate}=22 Ω, V_{CC}=15 V

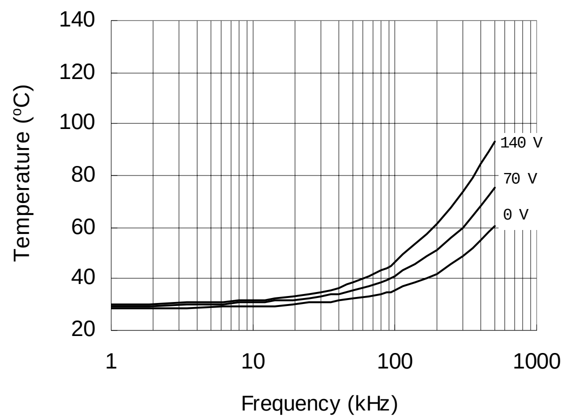


Figure 24. IRS2183 vs. Frequency (IRFBC40), R_{gate}=15 Ω, V_{CC}=15 V

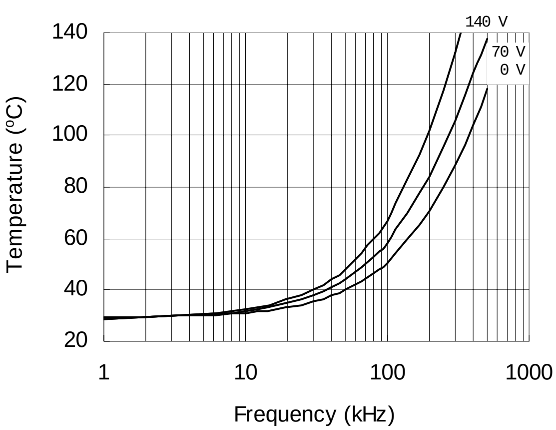


Figure 25. IRS2183 vs. Frequency (IRFPE50), R_{gate}=10 Ω, V_{CC}=15 V

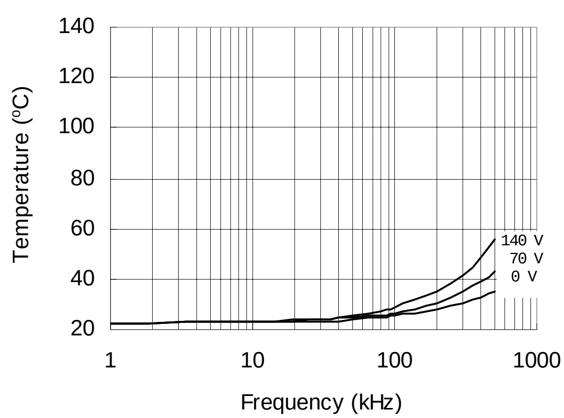


Figure 26. IRS21834 vs. Frequency (IRFBC20), R_{gate}=33 Ω, V_{CC}=15 V

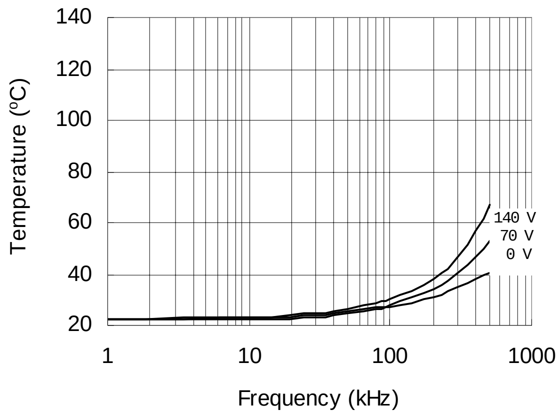


Figure 27. IRS21834 vs. Frequency (IRFBC30), R_{gate}=22 Ω, V_{CC}=15 V

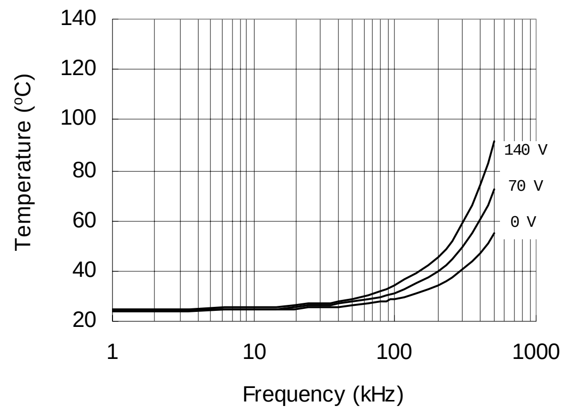


Figure 28. IRS21834 vs. Frequency (IRFBC40), R_{gate}=15 Ω, V_{CC}=15 V

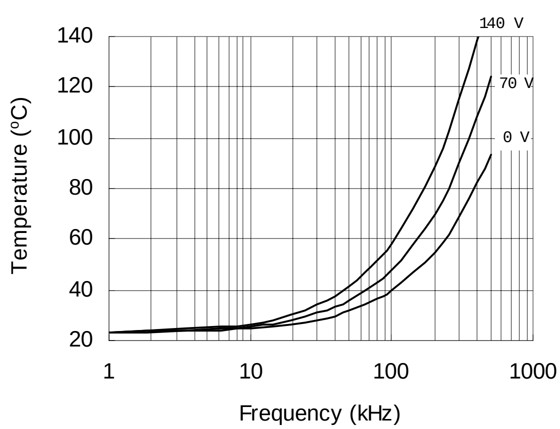


Figure 29. IRS21834 vs. Frequency (IRFPE50), R_{gate}=10 Ω, V_{CC}=15 V

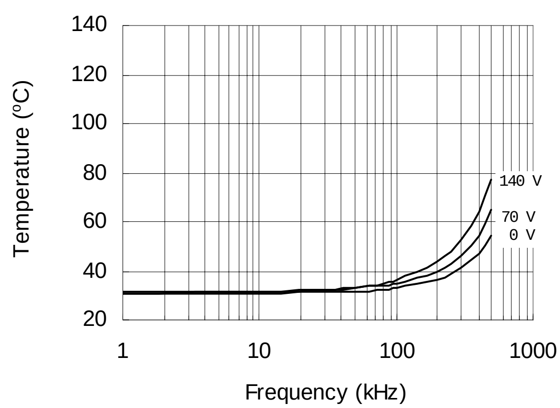


Figure 30. IRS2183S vs. Frequency (IRFBC20), R_{gate}=33 Ω, V_{CC}=15 V

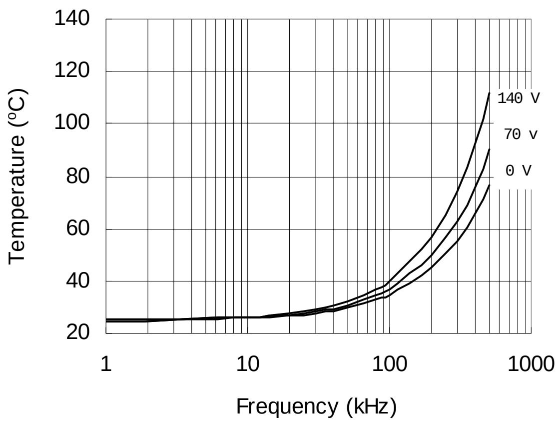


Figure 31. IRS2183S vs. Frequency (IRFBC30), R_{gate}=22 Ω, V_{CC}=15 V

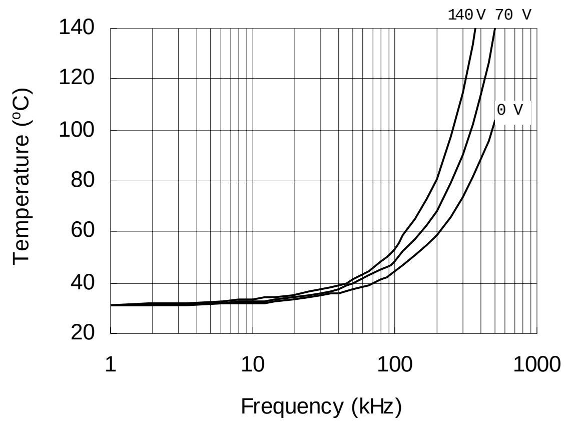


Figure 32. IRS2183S vs. Frequency (IRFBC40), R_{gate}=15 Ω, V_{CC}=15 V

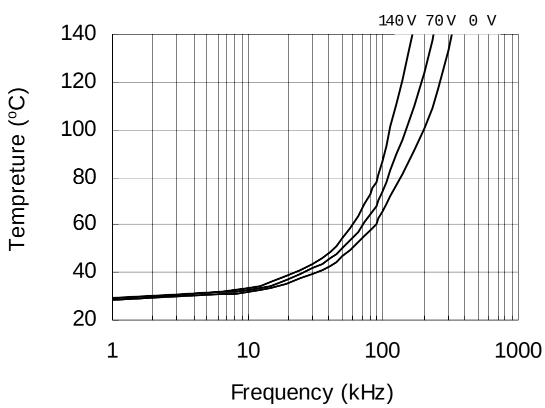


Figure 33. IRS2183S vs. Frequency (IRFPE50), R_{gate}=10 Ω, V_{CC}=15 V

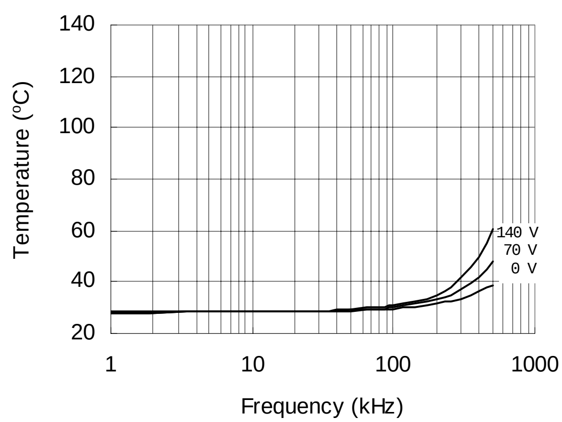


Figure 34. IRS21834S vs. Frequency (IRFBC20), R_{gate}=33 Ω, V_{CC}=15 V

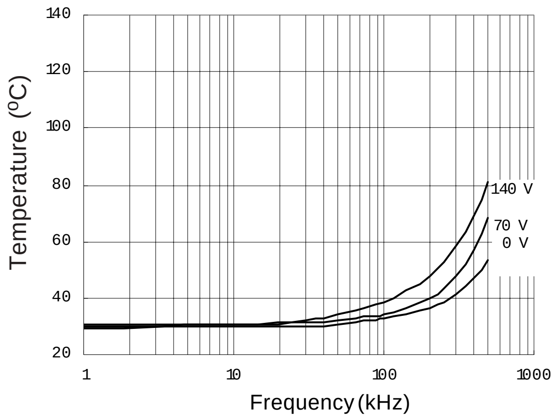


Figure 35. IRS21834S vs. Frequency (IRFBC30), R_{gate}=22 Ω, V_{CC}=15 V

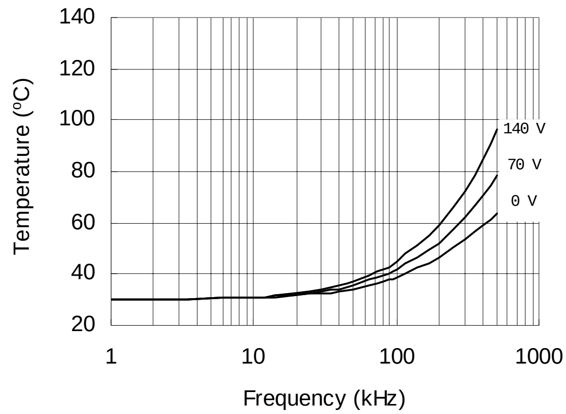


Figure 36. IRS21834S vs. Frequency (IRFBC40), R_{gate}=15 Ω, V_{CC}=15 V

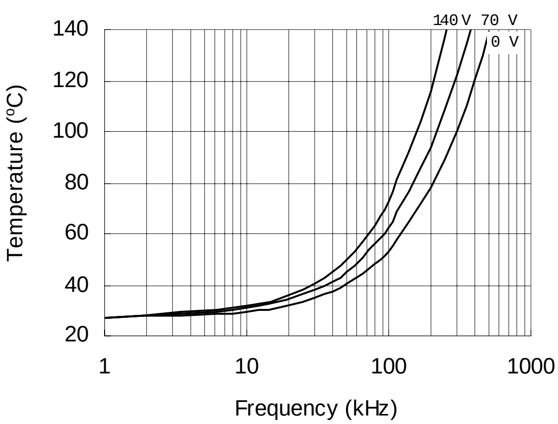
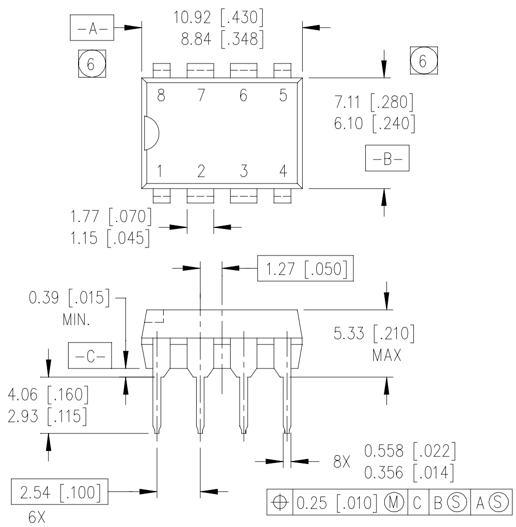
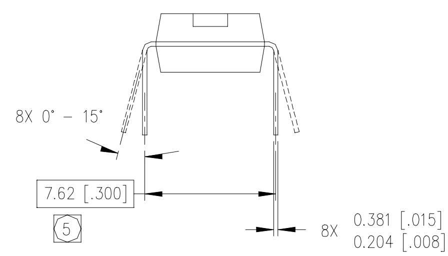


Figure 37. IRS21834S vs. Frequency (IRFPE50), R_{gate}=10 Ω, V_{CC}=15 V

Case outlines

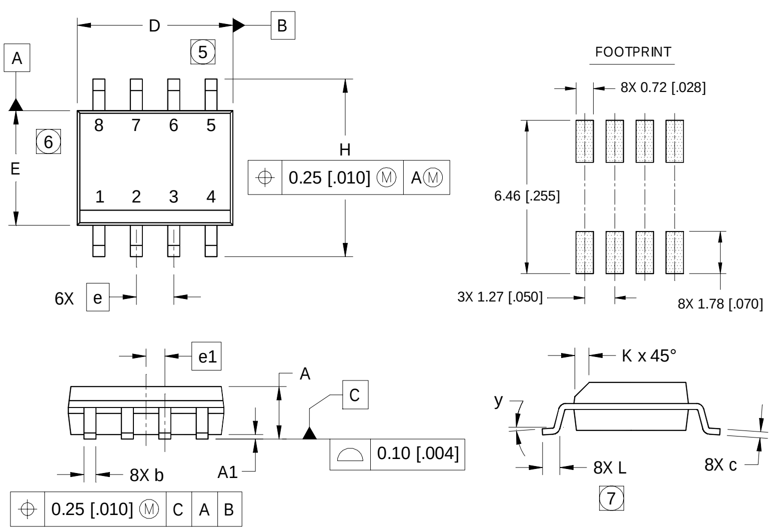


NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-001AB.
5. MEASURED WITH THE LEADS CONSTRAINED TO BE PERPENDICULAR TO DATUM PLANE C.
6. DIMENSION DOES NOT INCLUDE MOLD PROTUSIONS. MOLD PROTUSIONS SHALL NOT EXCEED 0.25 [.010].



8-Lead PDIP

01-6014
01-3003 01 (MS-001AB)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

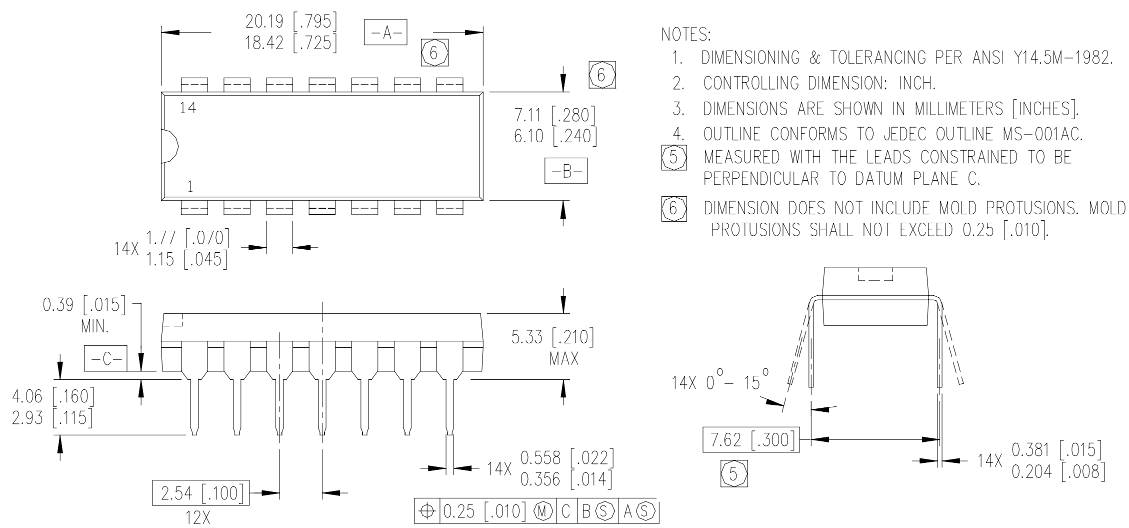
5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].

6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].

7 DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

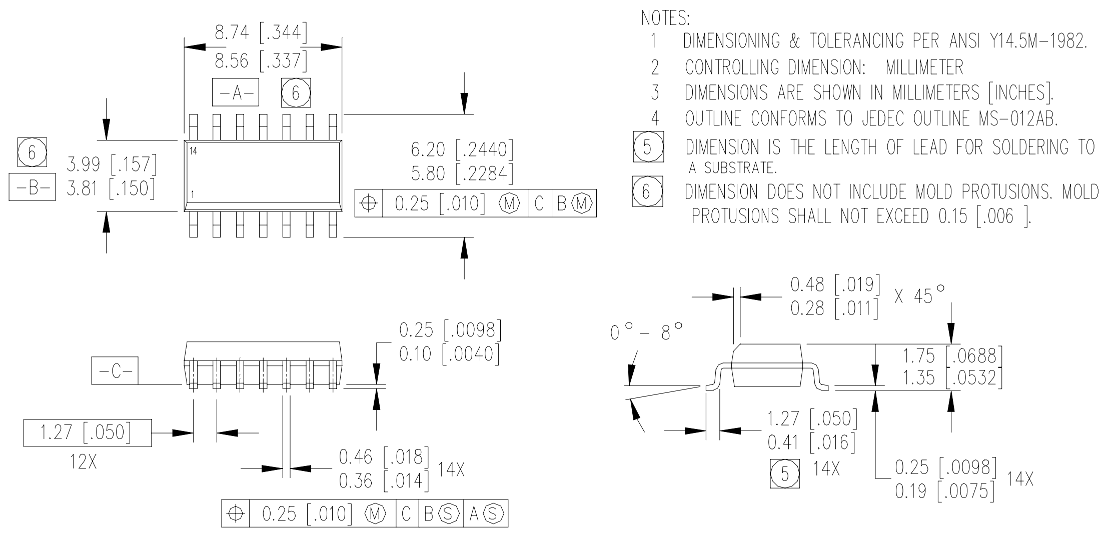
8-Lead SOIC

01-6027
01-0021 11 (MS-012AA)



14-Lead PDIP

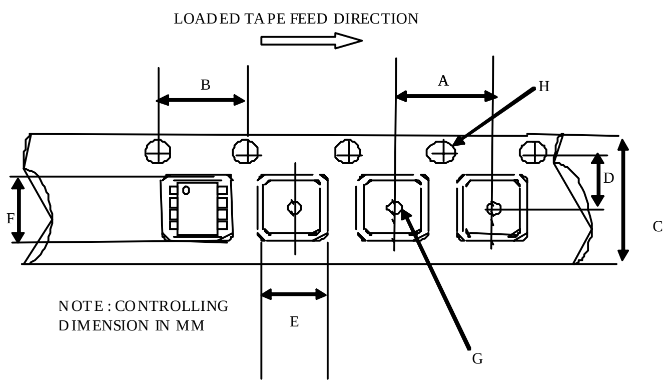
01-6010
01-3002 03 (MS-001AC)



14-Lead SOIC (narrow body)

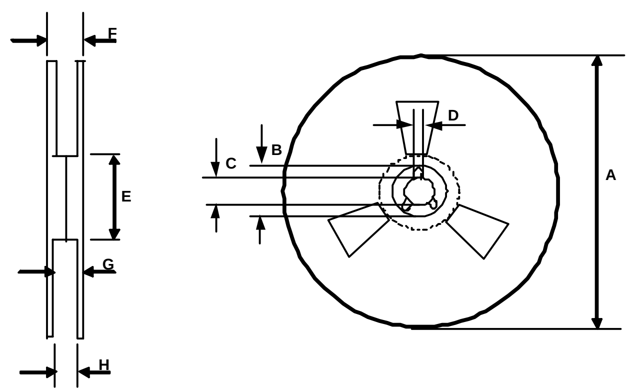
01-6019
01-3063 00 (MS-012AB)

Tape & Reel
8-lead SOIC



CARRIER TAPE DIMENSION FOR 8SOICN

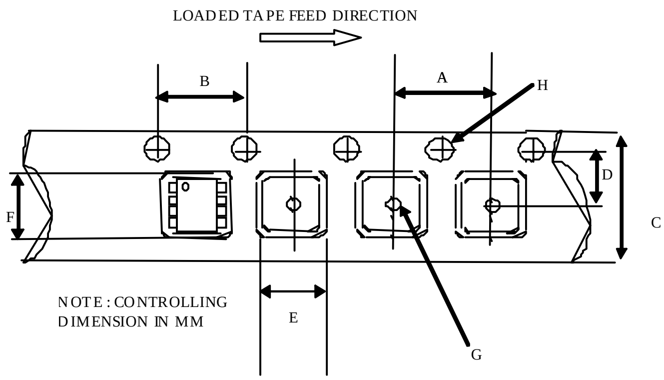
Code	Metric		Imperial	
	Min	Max	Min	Max
A	7.90	8.10	0.311	0.318
B	3.90	4.10	0.153	0.161
C	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
H	1.50	1.60	0.059	0.062



REEL DIMENSIONS FOR 8SOICN

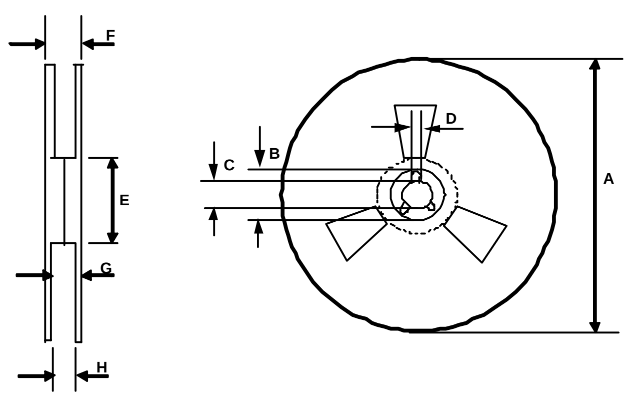
Code	Metric		Imperial	
	Min	Max	Min	Max
A	329.60	330.25	12.976	13.001
B	20.95	21.45	0.824	0.844
C	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
H	12.40	14.40	0.488	0.566

Tape & Reel
14-lead SOIC



CARRIER TAPE DIMENSION FOR 14SOICN

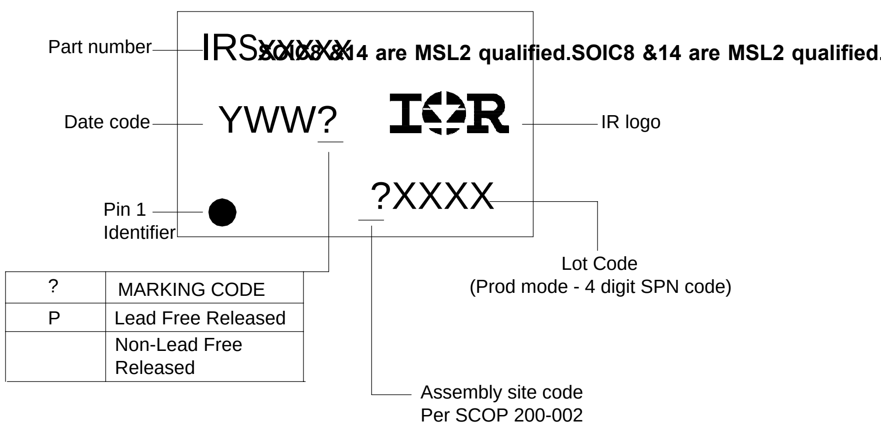
	Metric		Imperial	
Code	Min	Max	Min	Max
A	7.90	8.10	0.311	0.318
B	3.90	4.10	0.153	0.161
C	15.70	16.30	0.618	0.641
D	7.40	7.60	0.291	0.299
E	6.40	6.60	0.252	0.260
F	9.40	9.60	0.370	0.378
G	1.50	n/a	0.059	n/a
H	1.50	1.60	0.059	0.062



REEL DIMENSIONS FOR 14SOICN

	Metric		Imperial	
Code	Min	Max	Min	Max
A	329.60	330.25	12.976	13.001
B	20.95	21.45	0.824	0.844
C	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	22.40	n/a	0.881
G	18.50	21.10	0.728	0.830
H	16.40	18.40	0.645	0.724

LEADFREE PART MARKING INFORMATION



ORDER INFORMATION

8-Lead PDIP IRS2183PbF
8-Lead SOIC IRS2183SPbF
8-Lead SOIC Tape & Reel IRS2183STRPbF

14-Lead PDIP IRS21834PbF
14-Lead SOIC IRS21834SPbF
14-Lead SOIC Tape & Reel IRS21834STRPbF

International Rectifier

SOIC8 &14 are MSL2 qualified.
This product has been designed and qualified for the industrial level.
Qualification standards can be found at www.irf.com

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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Электронная почта: org@eplast1.ru
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